Silicon Carbide Schottky Diode 650 V, 10 A

FFSH1065B-F085

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 51 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 Qualified
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

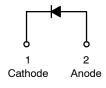
Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



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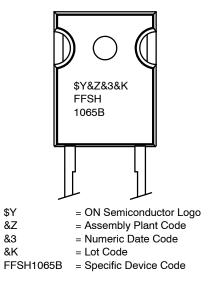


Schottky Diode



TO-247-2LD CASE 340DA

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSH1065B-F085

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	Repetitive Reverse Voltage		V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		51	mJ
١ _F	Continuous Rectified Forward Current @ T _C <	10	A	
	Continuous Rectified Forward Current @ T_C <	11.5		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	600	А
		T _C = 150°C, 10 μs	535	А
I _{F,SM}	Non-Repetitive Forward Surge Current $T_{C} = 25^{\circ}C$	Half-Sine Pulse, t _p = 8.3 ms	42	A
Ptot	Power Dissipation	$T_{C} = 25^{\circ}C$	83	W
		T _C = 150°C	14	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
	TO247 Mounting Torque, M3 Screw	60	Ncm	

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 51 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 14.5 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ extsf{ heta}JC}$			°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Мах	Unit
VF	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.5	1.7	V
		I _F = 10 A, T _C = 125°C	-	1.7	2.0	
		I _F = 10 A, T _C = 175°C	-	2	2.4	
I _R	Reverse Current	$V_{R} = 650 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	0.5	40	μΑ
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$	-	1	80	
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 175^{\circ}\text{C}$	-	2	160	
Q _C	Total Capacitive Charge	V = 400 V	-	25	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	421	-	pF
		V _R = 200 V, f = 100 kHz	-	40	-	1
		V _R = 400 V, f = 100 kHz	_	34	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH1065B-F085	FFSH1065B	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

FFSH1065B-F085

TYPICAL CHARACTERISTICS

(T_J = 25° C unless otherwise noted)

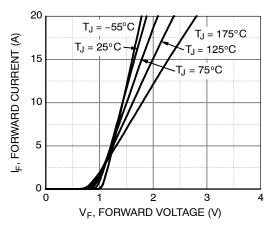


Figure 1. Forward Characteristics

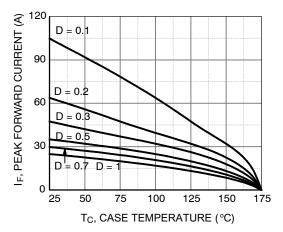


Figure 3. Current Derating

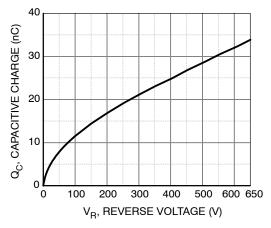


Figure 5. Capacitive Charge vs. Reverse Voltage

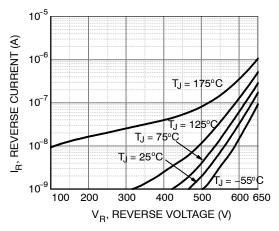
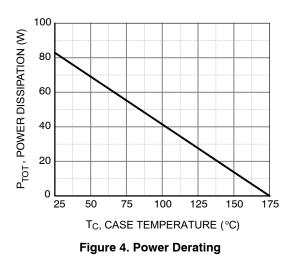


Figure 2. Reverse Characteristics



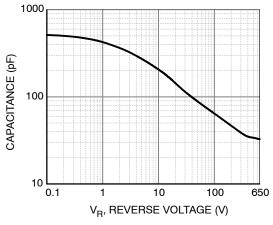
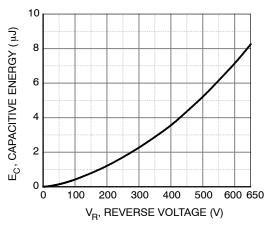


Figure 6. Capacitance vs. Reverse Voltage

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TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)





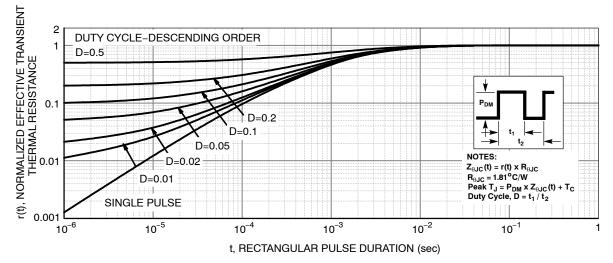
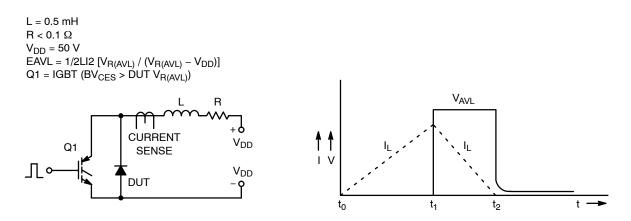


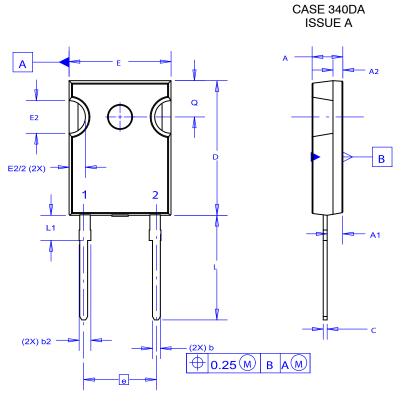
Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS



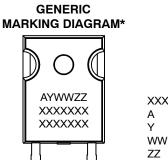






NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
- FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



XXXXX = Specific Device Code A = Assembly Location Y = Year

TO-247-2LD

V = Work Week

= Assembly Lot Code

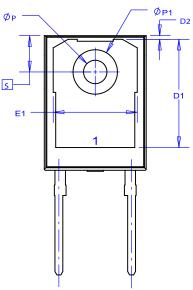
*This information is generic. Please refer to device data sheet for actual part marking. Pb– Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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 DESCRIPTION:
 TO-247-2LD
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	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A1	2.20	2.40	2.60		
A2	1.40	1.50	1.60		
b	1.17	1.26	1.35		
b2	1.53	1.65	1.77		
с	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	13.08	~	~		
D2	0.51	0.93	1.35		
E	15.37	15.62	15.87		
E1	12.81	~	~		
E2	4.96	5.08	5.20		
е	~	11.12	~		
L	15.75	16.00	16.25		
L1	3.69	3.81	3.93		
ØР	3.51	3.58	3.65		
Ø P1	6.60	6.80	7.00		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

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